

A QM/MM Study of Potential Steps in Direct Propylene Epoxidation Using H₂ and O₂ on Au/TS-1 Catalysts

Kendall T. Thomson*, Ajay Joshi, and W. Nicholas Delgass

Purdue University, School of Chemical Engineering, West Lafayette, Indiana, USA 47907

*thomsonk@ecn.purdue.edu

Introduction

Production of propylene oxide (PO) in a single step with no side products has been a long-sought industrial target. While a liquid-phase H₂O₂/TS-1 based route to PO appears imminent,¹ due to handling problems and cost associated with H₂O₂, researchers have also focused on direct gas-phase propylene oxidation using H₂ and O₂ over Au/Ti catalysts.²⁻⁴ The assumption that such catalysts operate by (1) H₂O₂ formation on Au and (2) propylene epoxidation on Ti using that H₂O₂ is supported by recent literature.^{5,6}

Materials and Methods

Since studies of Au/TS-1^{7,8} suggest that part of the epoxidation activity is associated with Au/Ti sites inside the zeolite channels, we have employed the hybrid quantum-mechanics/molecular-mechanics (QM/MM) approach—see Figure 1, augmented with full thermochemistry (298.15 K, 1 atm), to develop epoxidation mechanisms inside the TS-1 pores (5.5 Å). We considered both non-defect and Si-vacancy defect Ti-sites with and without Au₃ adsorbed⁹ on them and investigated OOH/H₂O₂ formation pathways.¹⁰

Results and Discussion

Consistent with experiments on Au/SiO₂,¹¹ we found that O₂ pre-adsorbed on Au₃ enhanced the dissociative adsorption of H₂ to form stable OOH species ($\Delta E_{\text{act}} = 7.7$ kcal/mol, Au₃/Ti-non-defect). We speculate that an H₂O₂ formation pathway similar to that found on gas-phase Au clusters^{12,13} is likely to operate on Au₃/Ti-non-defect sites—see Figure 2. H₂O₂ formed on these sites can then migrate to PO-producing sites via diffusion along the pore walls. Assuming such availability of H₂O₂, we modeled three different sites for propylene epoxidation: (1) Si-defect, (2) Ti-defect, and (3) Au₃-Ti-defect.¹⁰ We found that formation of Si-OOH species due to reaction of H₂O₂ with a metal-vacancy Si-defect sites is both kinetically ($\Delta E_{\text{act}} = 33.2$ kcal/mol) and thermodynamically unfavorable ($\Delta E = +2.8$ kcal/mol). However, it is much easier ($\Delta E_{\text{act}} = 16.8$ kcal/mol) to form Ti-OOH species (and water) by attacking the Ti-defect site with H₂O₂ ($\Delta E = -8.0$ kcal/mol). Propylene reacts with these Ti-OOH species to form propylene oxide with $\Delta E_{\text{act}} = 15.8$ kcal/mol and $\Delta E = -51.3$ kcal/mol. Interestingly, we predict that the activation barrier to form Ti-OOH species on Au₃/Ti-defect sites is significantly higher ($\Delta E_{\text{act}} = 28.1$ kcal/mol) than that for the Ti-defect site without Au₃ and that OOH species formed on Au₃ in an Au₃/Ti-defect site are likely to decompose rapidly to form water ($\Delta E_{\text{act}} = 1.3$ kcal/mol) due to strong interaction with the silanol (Si-OH) groups around the defect. Thus, we conclude that the sequential propylene epoxidation pathway is kinetically unfavorable on the Au₃/Ti-defect site but is favorable with a combination of Au₃/Ti-non-defect and Ti-defect sites.

Significance

The commercialization of a gas-phase heterogeneous catalyst for production of propylene oxide would lead to more environmentally friendly processes in what is a \$9+ billion per year industry. Understanding the underlying mechanisms for these systems is an important step for improving catalytic properties.

Figure 1

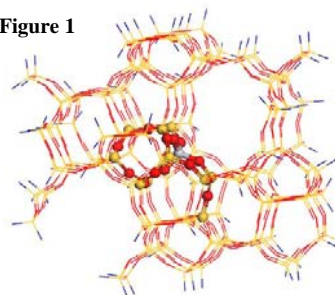


Figure 2

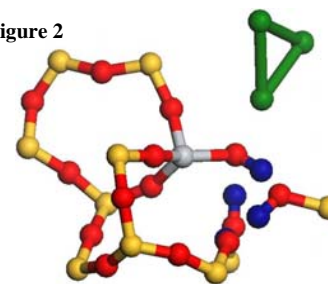


Figure 1. QM/MM molecular model of a Ti/Si-vacancy site in the TS-1 lattice.

Figure 2. Au₃ cluster anchored near a Si-vacancy site (defect) adjacent to Ti in TS-1 lattice.

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